

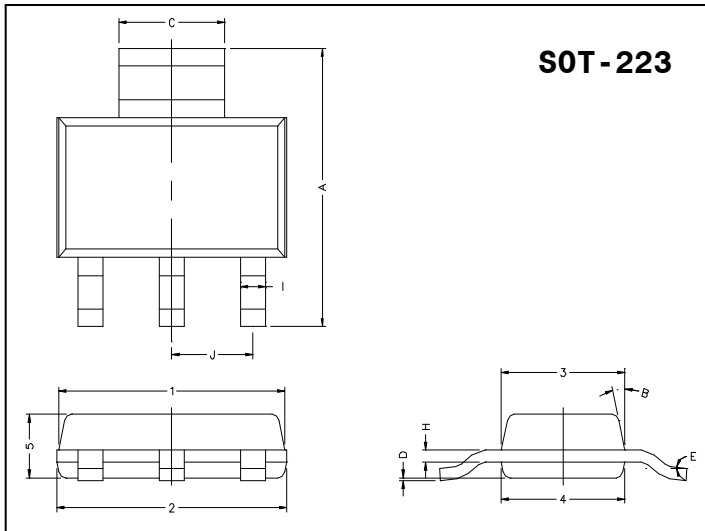
## GL5551

### NPN EPITAXIAL PLANAR TRANSISTOR

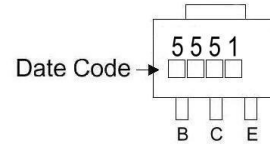
#### Description

The GL5551 is designer for general purpose applications requiring high breakdown voltages.

#### Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13° TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T <sub>j</sub>	+150	°C
Storage Temperature	T <sub>stg</sub>	-55 ~ +150	°C
Collector to Base Voltage	VCBO	180	V
Collector to Emitter Voltage	VCEO	160	V
Emitter to Base Voltage	VEBO	6	V
Collector Current	I <sub>C</sub>	600	mA
Total Power Dissipation	PD	1.5	W

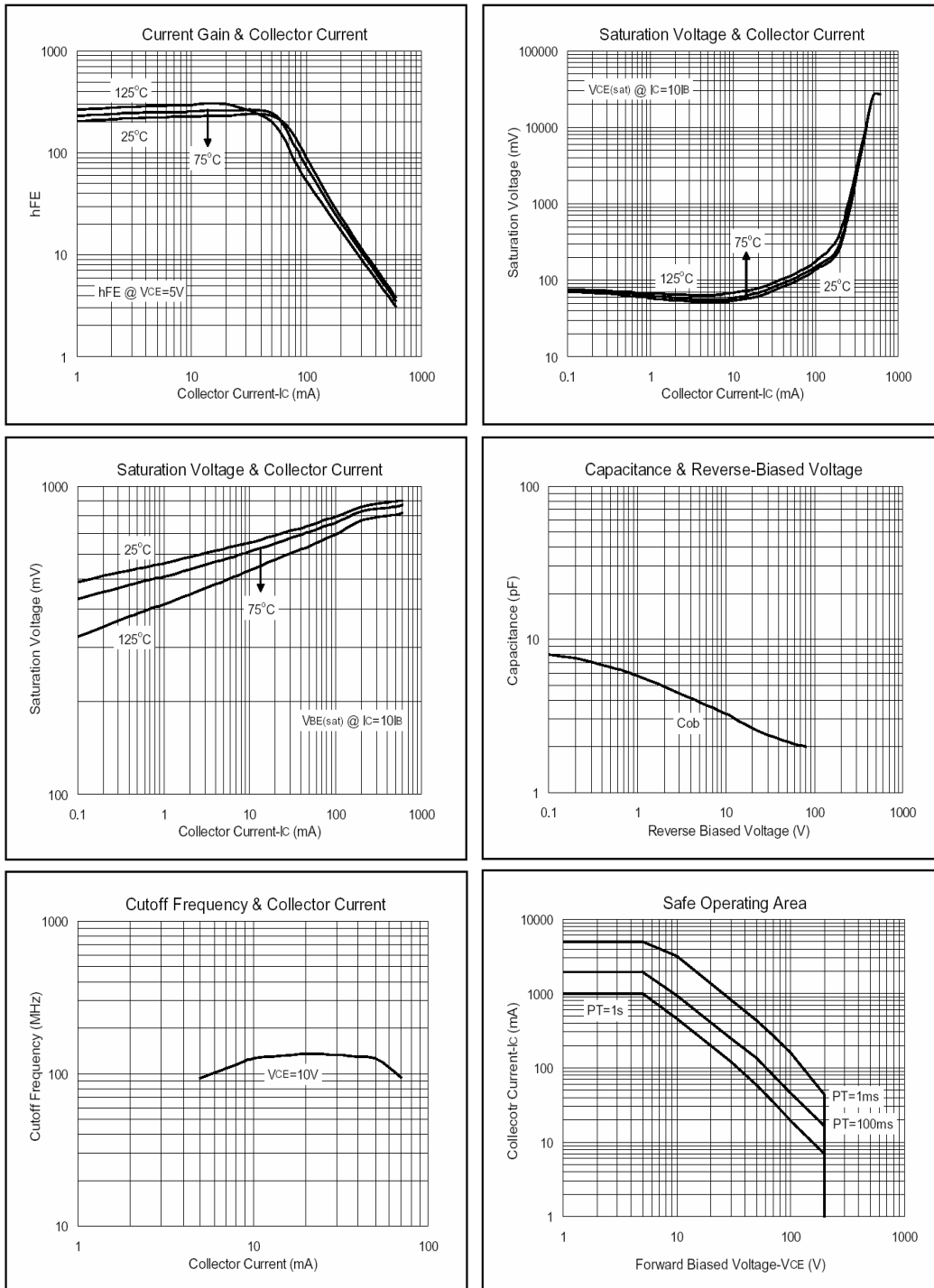
#### Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	180	-	-	V	I <sub>C</sub> =100μA, I <sub>E</sub> =0
BVCEO	160	-	-	V	I <sub>C</sub> =1.0mA, I <sub>B</sub> =0
BVEBO	6	-	-	V	I <sub>E</sub> =10μA, I <sub>C</sub> =0
ICBO	-	-	50	nA	V <sub>CB</sub> =120V, I <sub>E</sub> =0
IEBO	-	-	50	nA	V <sub>EB</sub> =4V, I <sub>C</sub> =0
VCE(sat)1	-	-	0.15	V	I <sub>C</sub> =10mA, I <sub>B</sub> =1.0mA
VCE(sat)2	-	-	0.2	V	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA
VBE(sat)1	-	-	1	V	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA
VBE(sat)2	-	-	1	V	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA
hFE1	80	-	-		V <sub>CE</sub> =5V, I <sub>C</sub> =1mA
hFE2	80	160	400		V <sub>CE</sub> =5V, I <sub>C</sub> =10mA
hFE3	50	-	-		V <sub>CE</sub> =5V, I <sub>C</sub> =50mA
f <sub>T</sub>	100	-	300	MHz	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA, f=100MHz
C <sub>ob</sub>	-	-	6	pF	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz

#### Classification Of hFE

Rank	A	N	C
Range	80 - 200	100 - 250	160 - 400

## Characteristics Curve



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